Electronic Supplementary Information (ESI)

Halogen bond-directed self-assembly in bicomponent blends at the solid/liquid interface: Effect of the alkyl chain substitution position

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Additional STM images

*STM images of **Py-3,4/FI-3,5** blend with different blend ratio*

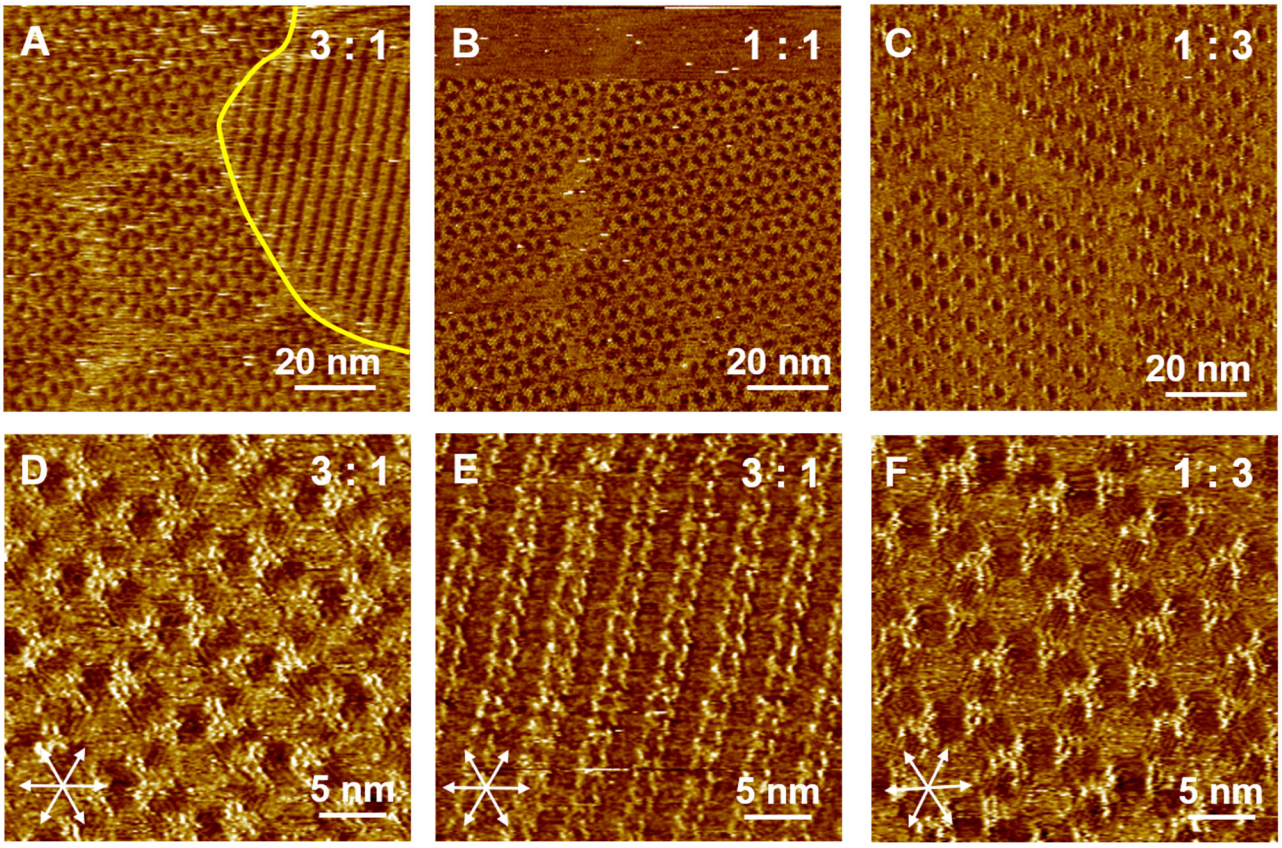

Fig. S1 STM images of the bicomponent blend of **Py-3,4/FI-3,5** blend with different blend ratio. A set of arrows in (D) − (F) indicates the HOPG lattice directions. The blend molar ratio is shown at the right corner of each image. Panels (D) and (E) are the enlarged images of (A), in which the hexagonal pattern and double columnar structures are observed, respectively. Panel (F) is the magnified image of panel (C). Tunnelling conditions: (A) I = 25 pA, V = −566 mV; (B) I = 25 pA, V = −1100 mV; (C) I = 25 pA, V = −201 mV; (D) I = 50 pA, V = −500 mV; (E) I = 50 pA, V = −566 mV; and (F) I =25 pA, V = −201 mV.

*STM images of **Py-3,5/FI-3,4** blend with different blend ratio*

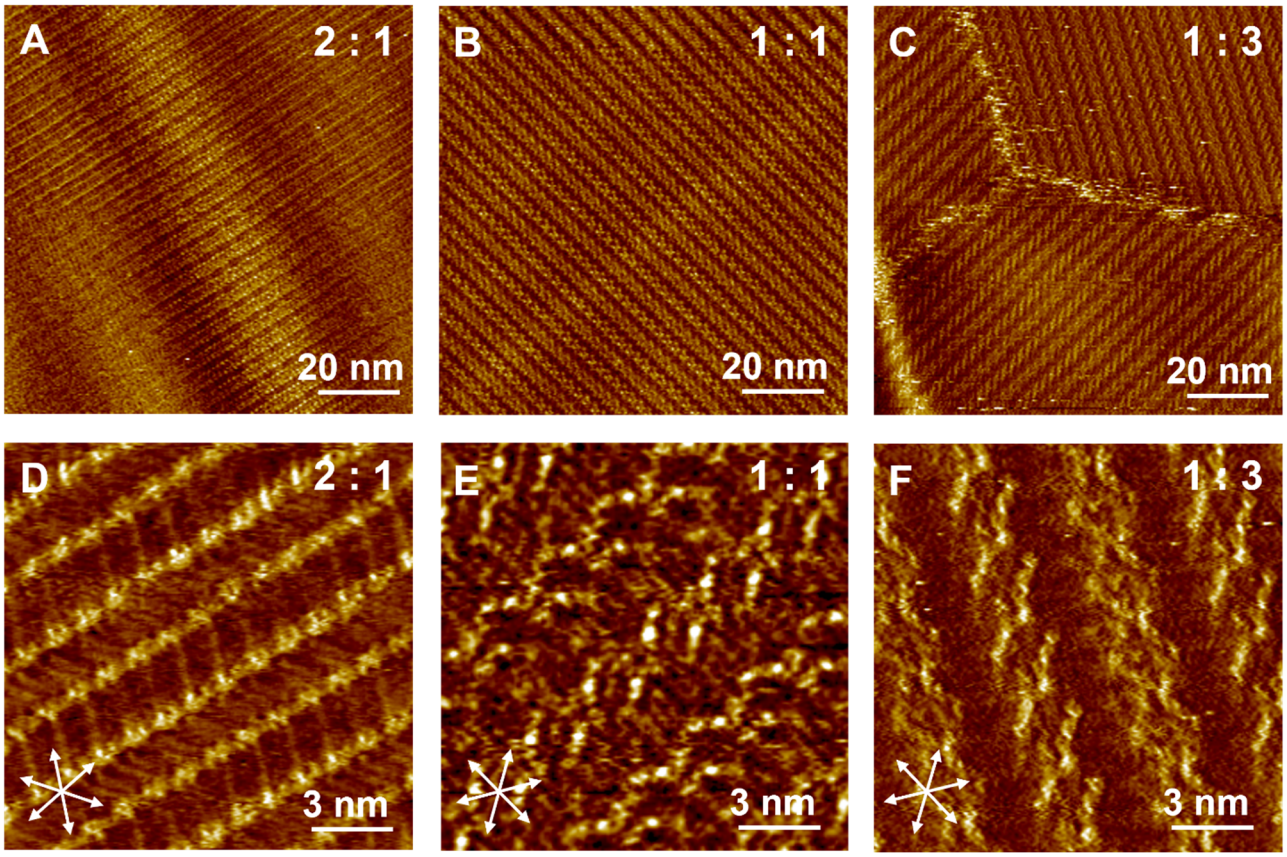

Fig. S2 STM images of the bicomponent blend of **Py-3,5/FI-3,4** blend with different blend ratio. A set of arrows in (D) − (F) indicates the HOPG lattice directions. The blend molar ratio is shown at the right corner of each image. Panels (D) − (F) are the enlarged images of (A) − (C), respectively. Tunnelling conditions: (A) I = 50 pA, V = −909 mV; (B) I = 25 pA, V = −292 mV; (C) I = 25 pA, V = −1000 mV; (D) I = 50 pA, V = −909 mV; (E) I = 50 pA, V = −707 mV; and (F) I =25 pA, V = −1000 mV.